

FQPF19N20

N-Channel QFET® MOSFET

200 V, 11.8 A, 150 mΩ

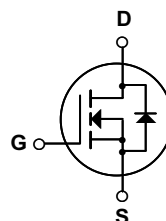
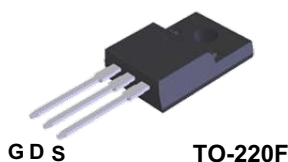


Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 11.8 A, 200 V, $R_{DS(on)}=150\text{ m}\Omega(\text{Max.})@V_{GS}=10\text{ V}, I_D=5.9\text{ A}$
- Low Gate Charge (Typ. 31 nC)
- Low C_{rss} (Typ. 30 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | FQPF19N20 | Unit |
|----------------|---|-------------|---------------------|
| V_{DSS} | Drain-Source Voltage | 200 | V |
| I_D | Drain Current - Continuous ($T_C = 25^\circ\text{C}$) | 11.8 | A |
| | - Continuous ($T_C = 100^\circ\text{C}$) | 7.5 | A |
| I_{DM} | Drain Current - Pulsed (Note 1) | 48 | A |
| V_{GSS} | Gate-Source Voltage | ± 30 | V |
| E_{AS} | Single Pulsed Avalanche Energy (Note 2) | 250 | mJ |
| I_{AR} | Avalanche Current (Note 1) | 11.8 | A |
| E_{AR} | Repetitive Avalanche Energy (Note 1) | 5.0 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 5.5 | V/ns |
| P_D | Power Dissipation ($T_C = 25^\circ\text{C}$) | 50 | W |
| | - Derate above 25°C | 0.4 | W/ $^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +150 | $^\circ\text{C}$ |
| T_L | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 300 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | Typ | Max | Unit |
|-----------------|---|-----|------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | -- | 2.5 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | -- | 62.5 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics T_C = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|-----|------|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0 V, I _D = 250 μA | 200 | -- | -- | V |
| ΔBV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced to 25°C | -- | 0.18 | -- | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 200 V, V _{GS} = 0 V | -- | -- | 1 | μA |
| | | V _{DS} = 160 V, T _C = 125°C | -- | -- | 10 | μA |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 30 V, V _{DS} = 0 V | -- | -- | 100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -30 V, V _{DS} = 0 V | -- | -- | -100 | nA |

On Characteristics

| | | | | | | |
|---------------------|-----------------------------------|---|-----|------|------|---|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250 μA | 3.0 | -- | 5.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | V _{GS} = 10 V, I _D = 5.9 A | -- | 0.12 | 0.15 | Ω |
| g _{FS} | Forward Transconductance | V _{DS} = 40 V, I _D = 5.9 A (Note 4) | -- | 8.7 | -- | S |

Dynamic Characteristics

| | | | | | | |
|------------------|------------------------------|---|----|------|------|----|
| C _{iss} | Input Capacitance | V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz | -- | 1220 | 1600 | pF |
| C _{oss} | Output Capacitance | | -- | 220 | 290 | pF |
| C _{rss} | Reverse Transfer Capacitance | | -- | 30 | 40 | pF |

Switching Characteristics

| | | | | | | |
|---------------------|---------------------|--|----|------|-----|----|
| t _{d(on)} | Turn-On Delay Time | V _{DD} = 100 V, I _D = 19.4 A, R _G = 25 Ω (Note 4, 5) | -- | 20 | 50 | ns |
| t _r | Turn-On Rise Time | | -- | 190 | 390 | ns |
| t _{d(off)} | Turn-Off Delay Time | | -- | 55 | 120 | ns |
| t _f | Turn-Off Fall Time | | -- | 80 | 170 | ns |
| Q _g | Total Gate Charge | V _{DS} = 160 V, I _D = 19.4 A, V _{GS} = 10 V (Note 4, 5) | -- | 31 | 40 | nC |
| Q _{gs} | Gate-Source Charge | | -- | 8.6 | -- | nC |
| Q _{gd} | Gate-Drain Charge | | -- | 13.5 | -- | nC |

Drain-Source Diode Characteristics and Maximum Ratings

| | | | | | | |
|-----------------|---|---|----|------|-----|----|
| I _S | Maximum Continuous Drain-Source Diode Forward Current | -- | -- | 11.8 | A | |
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | -- | -- | 48 | A | |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0 V, I _S = 11.8 A | -- | -- | 1.5 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = 19.4 A, di _F / dt = 100 A/μs (Note 4) | -- | 140 | -- | ns |
| Q _{rr} | Reverse Recovery Charge | | -- | 0.69 | -- | μC |

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 2.7mH, I_{AS} = 11.8A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 19.4A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

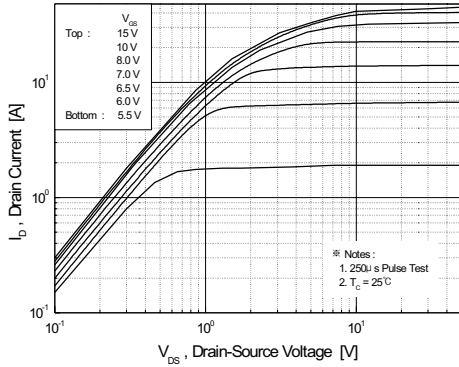


Figure 1. On-Region Characteristics

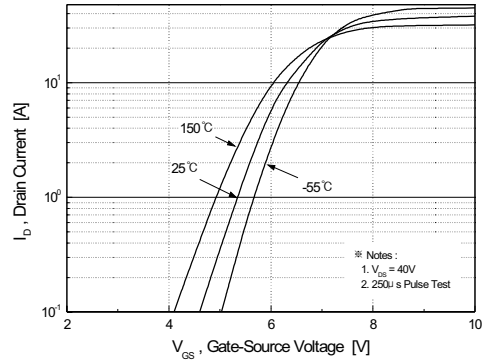


Figure 2. Transfer Characteristics

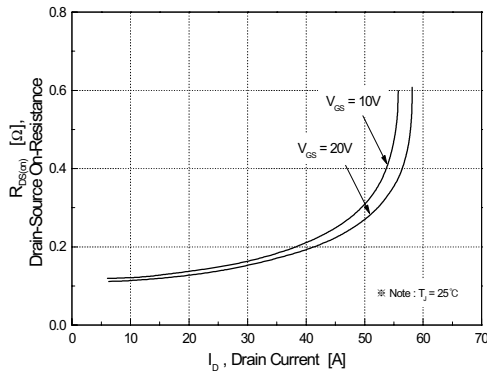


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

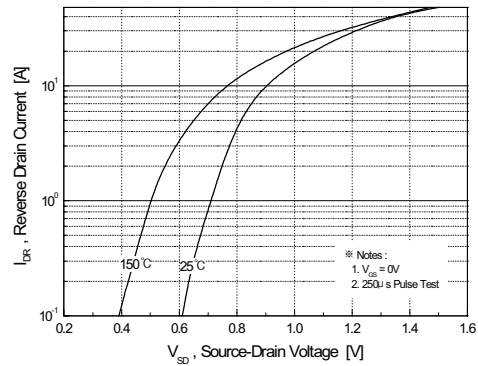


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

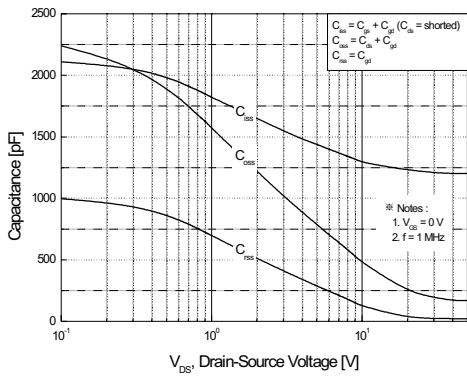


Figure 5. Capacitance Characteristics

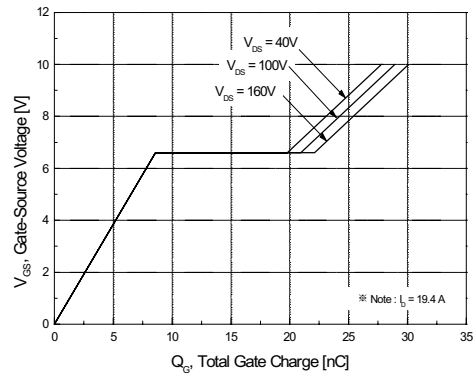


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

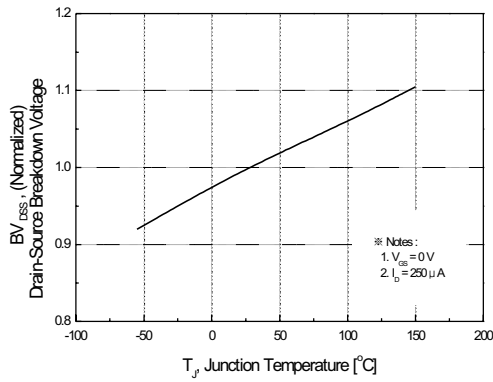


Figure 7. Breakdown Voltage Variation vs. Temperature

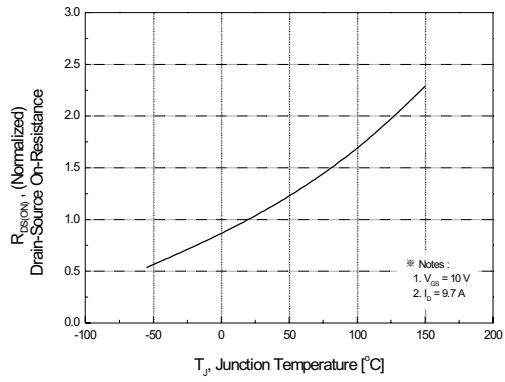


Figure 8. On-Resistance Variation vs. Temperature

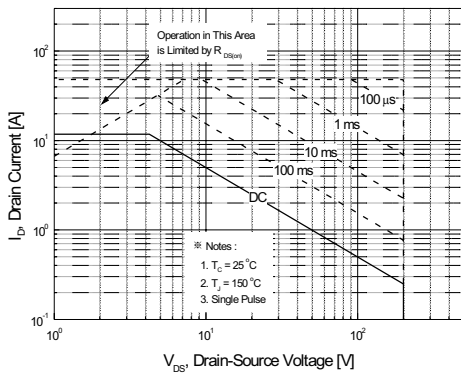


Figure 9. Maximum Safe Operating Area

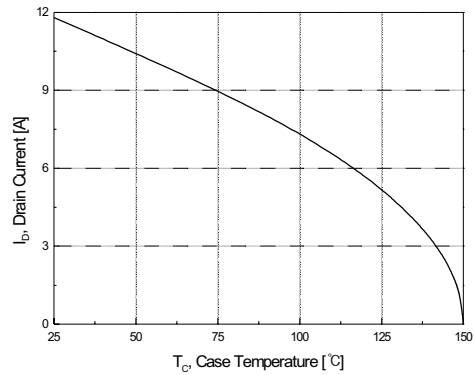


Figure 10. Maximum Drain Current vs. Case Temperature

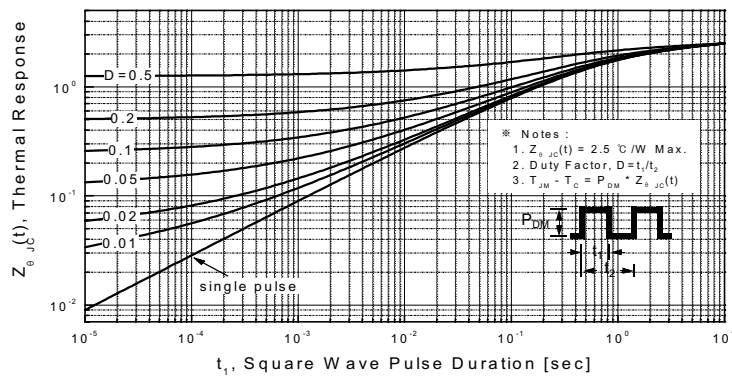
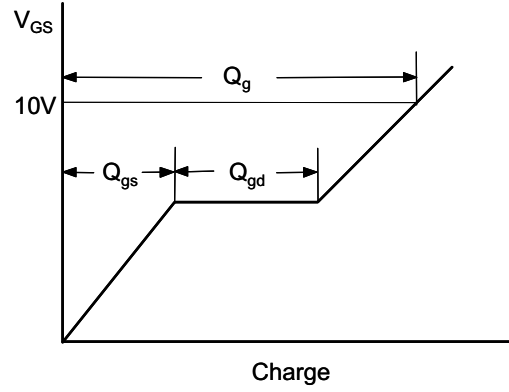
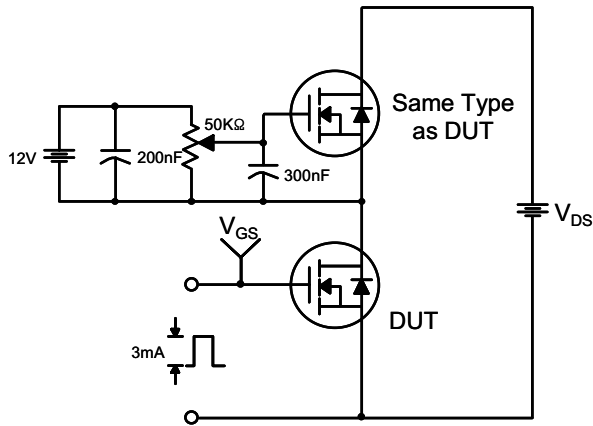
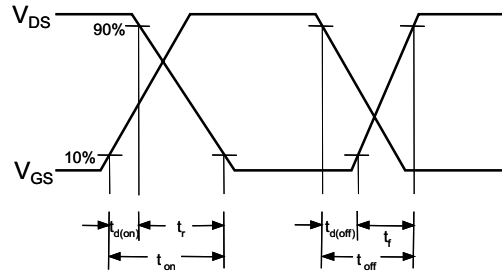
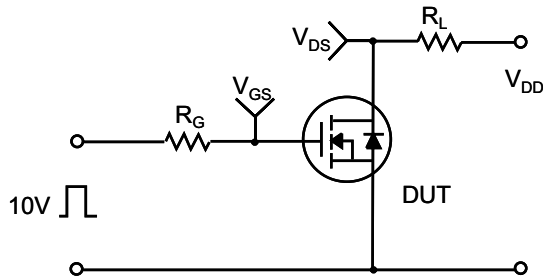


Figure 11. Transient Thermal Response Curve

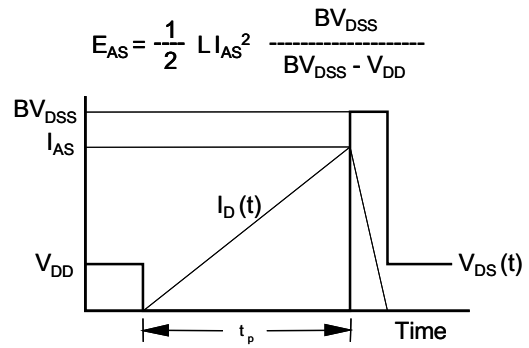
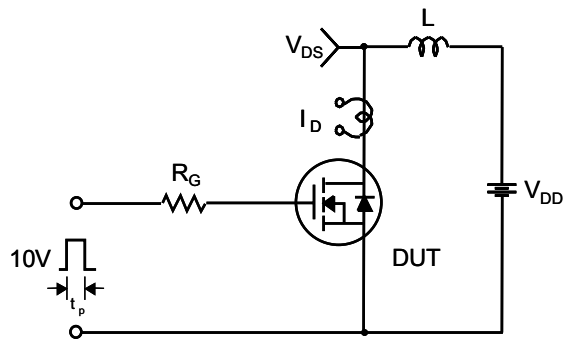
Gate Charge Test Circuit & Waveform



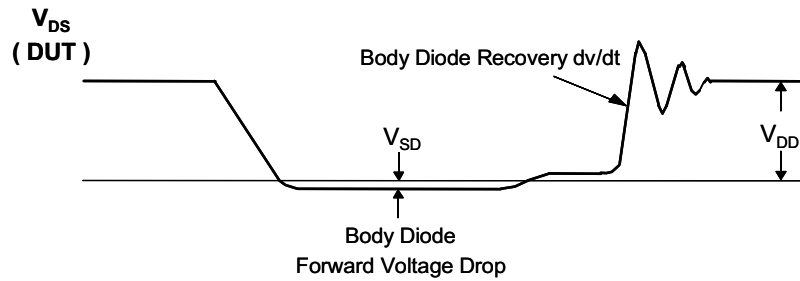
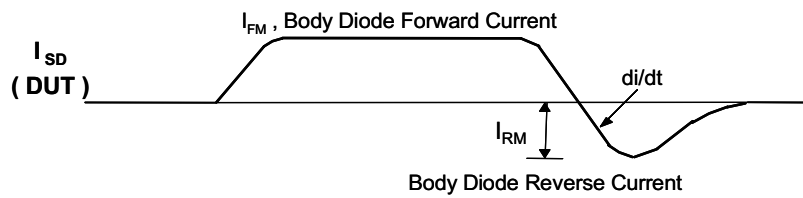
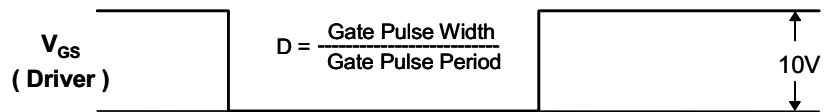
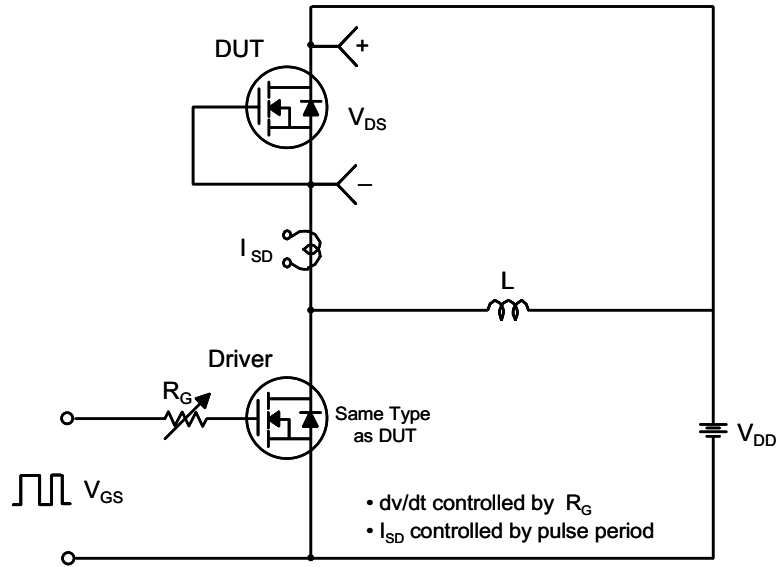
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

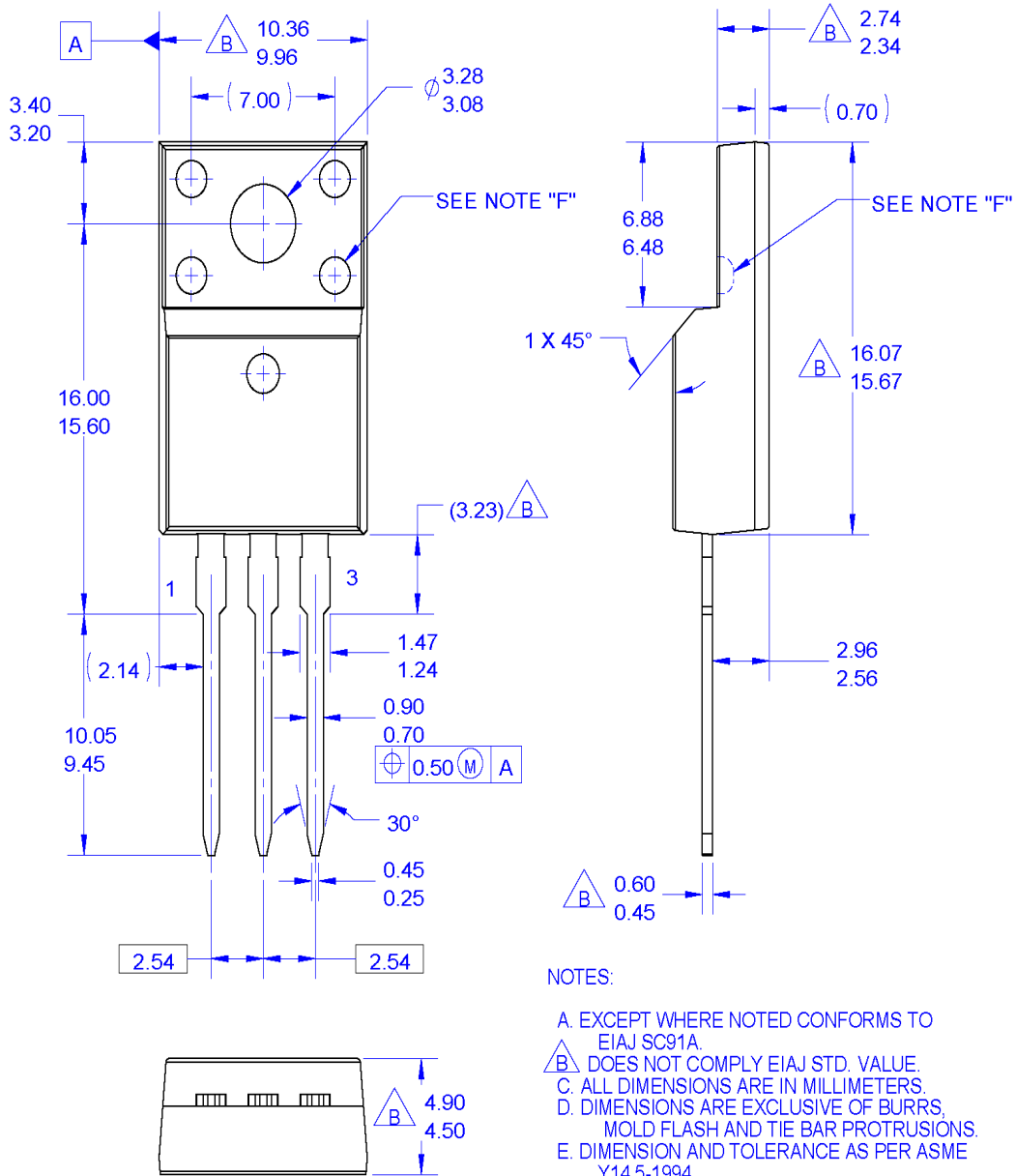


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-220F



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

Dimensions in Millimeters



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| | SmartMax™ | |
| | SMART START™ | |
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Rev. I64